ICMOVPE
XXII July 12-17, 2026
ICC JEJU, Jeju Island, Korea

Session Title:	**[WeB3] Nitrides for Electronics - III**
Session Date:	**July 15 (Wed.), 2026**
Session Time:	**15:35-17:05**
Session Room:	**Room B (Baekrok Hall B-2, 1F)**
Session Chairs	

[WeB3-1] **15:35-15:50**

In-Depth Study of Localised Growth of GaN on Silicon Leading to 1 kV, 5 mOhm.cm^2 Vertical Diodes

M. Charles[1], D. Plaza-Arguello[1], M. El Amrani[1], T. Kaltsounis[1], H. El Rammouz[1], Z. M'Qaddem[1], T. Guillemin[2], S. Torrengo[1], M. Lafossas[1], N. Rochat[1], Y. Cordier[2], and J. Buckley[1], [1] CEA Leti, France, [2] Univ. Côte d'Azur, France

[WeB3-2] **15:50-16:05**

Investigating the Impact of High-Temperature Ohmic Contact Annealing on AlN Schottky Barrier Diodes

Haicheng Cao[1], Mingtao Nong[1], Tingang Liu[1], Zixian Jiang[1], Zhiyuan Liu[1], Saravanan Yuvaraja[1], Xiao Tang[2], Biplab Sarkar[3], Ying Wu[1], and Xiaohang Li[1], [1] King Abdullah University of Science and Technology, Saudi Arabia, [2] University of Bristol, United Kingdom, [3] Indian Institute of Technology, India

[WeB3-3] **16:05-16:20**

Submicron Ultrafast Raman Thermography System for Power Semiconductor Devices and Next Generation Semiconductors.

Jung-Hoon Song[1,2], Youngboo Moon[1,3], Seungyoung Lim[1], Gye Eun Choi[1], and Jaesun Kim[1], [1] AccuOptotec Co., Korea, [2] Kongju National University, Korea, [3] UJL Co., Korea

[WeB3-4] **16:20-16:35**

Understanding the Impact of n-Type GaN Drift Layer Growth Conditions on 300 mm Wafer Bow for GaN-on-Si Vertical Devices

G. Bouhet, F. Barbier, C. Vergnaud, H. El Rammouz, A. Chaumont, M. Lafossas, P. Valentin, V. Balan, A. Olivier, J. Buckley, C. Masante, M. Charles, and S. Torrengo, CEA-Leti, France

[WeB3-5] **16:35-16:50**

SiOx Interlayer for Reverse Current Suppression in p-GaN Diodes

Zixian Jiang and Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[WeB3-6] **16:50-17:05**

Crack-Free Si-Doped AlN on Si(111) for Fully Vertical AlN Schottky Barrier Diodes

Haicheng Cao[1], Mingtao Nong[1], Xiao Tang[2], Biplab Sarkar[3], Ying Wu[1], and Xiaohang Li[1], [1] King Abdullah University of Science and Technology, Saudi Arabia, [2] University of Bristol, United Kingdom, [3] Indian Institute of Technology, India